



### Dual P-Channel 1.8-V (G-S) MOSFET

#### CHARACTERISTICS

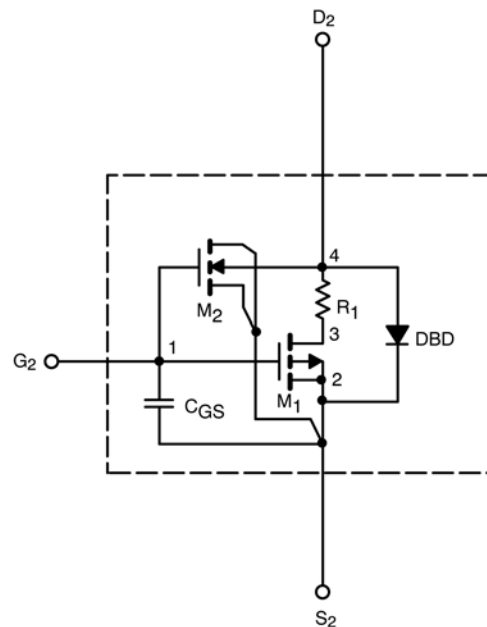
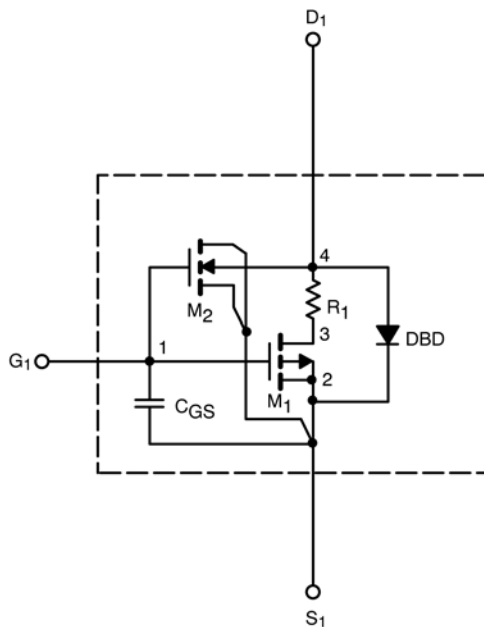
- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the  $-55$  to  $125^{\circ}\text{C}$  Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

#### DESCRIPTION

The attached spice model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the  $-55$  to  $125^{\circ}\text{C}$  temperature ranges under the pulsed 0-V to 5-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

# SPICE Device Model Si1907DL

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SPECIFICATIONS ( $T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Test Condition	Simulated Data	Measured Data	Unit
<b>Static</b>					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\ \mu\text{A}$	0.78		V
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\ \text{V}$ , $V_{GS} = -4.5\ \text{V}$	5.8		A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}$ , $I_D = -0.53\ \text{A}$	0.54	0.57	$\Omega$
		$V_{GS} = -2.5\ \text{V}$ , $I_D = -0.44\ \text{A}$	0.77	0.80	
		$V_{GS} = -1.8\ \text{V}$ , $I_D = -0.20\ \text{A}$	1.05	1.25	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\ \text{V}$ , $I_D = -0.53\ \text{A}$	1.19	1.1	S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -0.23\ \text{A}$ , $V_{GS} = 0\ \text{V}$	-0.76	-0.80	V
<b>Dynamic<sup>b</sup></b>					
Total Gate Charge	$Q_g$	$V_{DS} = -6\ \text{V}$ , $V_{GS} = -4.5\ \text{V}$ , $I_D = -0.53\ \text{A}$	0.72	1.5	nC
Gate-Source Charge	$Q_{gs}$		0.14	0.40	
Gate-Drain Charge	$Q_{gd}$		0.12	0.25	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\ \text{V}$ , $R_L = 12\ \Omega$ $I_D \cong -0.50\ \text{A}$ , $V_{GEN} = -4.5\ \text{V}$ , $R_G = 6\ \Omega$	6	6	ns
Rise Time	$t_r$		7	20	
Turn-Off Delay Time	$t_{d(off)}$		23	10	
Fall Time	$t_f$		7	10	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = -0.23\ \text{A}$ , $di/dt = 100\ \mu\text{s}$	15	20	

### Notes

a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

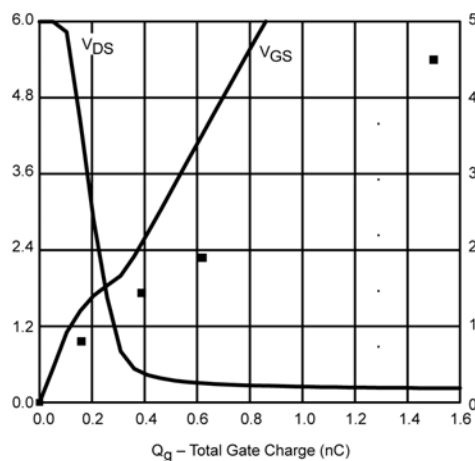
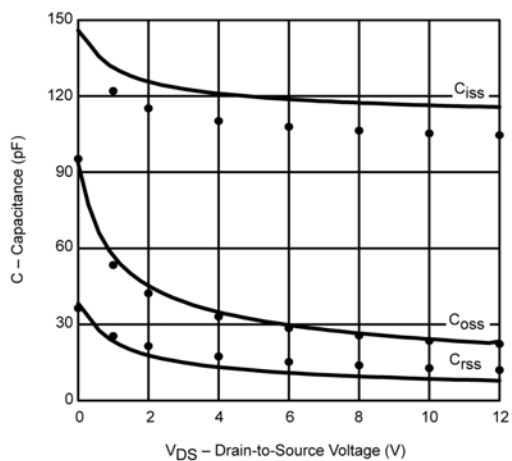
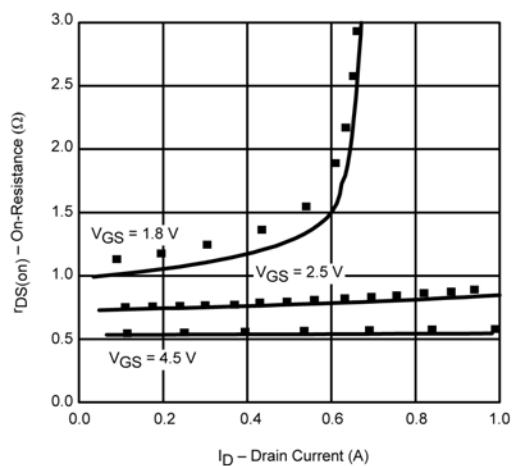
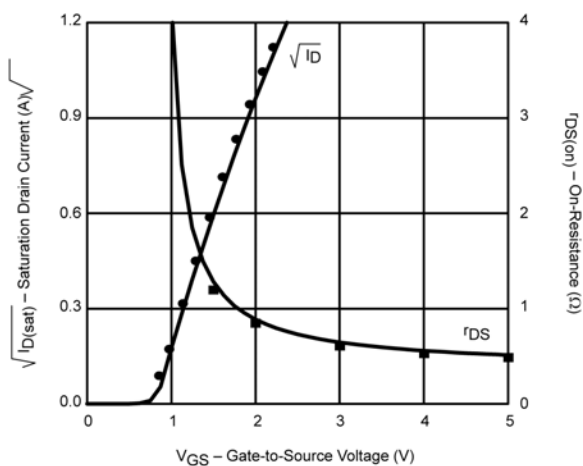
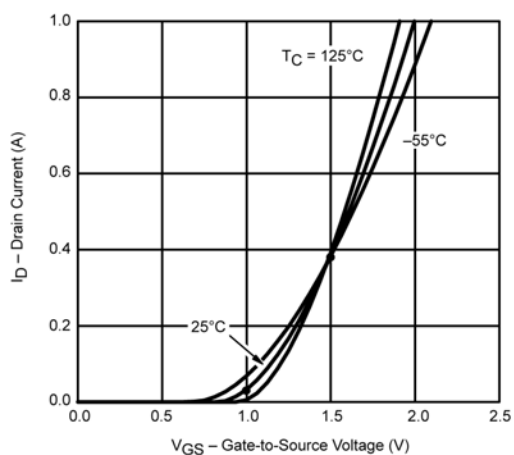
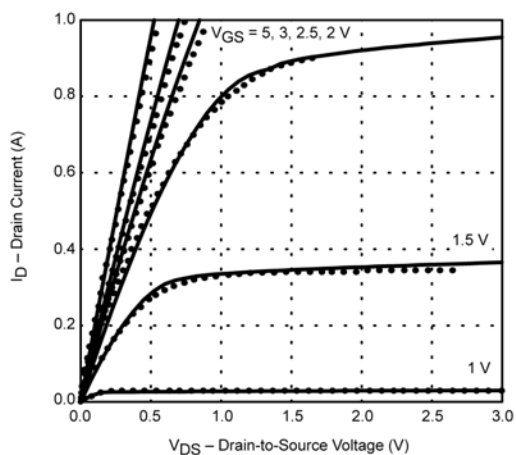
b. Guaranteed by design, not subject to production testing.



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COMPARISON OF MODEL WITH MEASURED DATA ( $T_J=25^\circ\text{C}$  UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.